

Serial No. 09/008,531
MIO 0012 V2

Appendix

In the Claims

31. (Twice Amended) A process for making a semiconductor device comprising:
- providing a substrate having at least one semiconductor layer;
 - forming an opening in said at least one semiconductor layer, wherein said opening includes sidewalls;
 - forming a conductive layer over said at least one semiconductor layer and said opening so that said conductive layer has a [having] topography that includes a substantially vertical component;
 - forming an overlayer over said conductive layer;
 - forming a contact in said overlayer and in said vertical component disposed adjacent to and contacting said vertical component; and
 - [forming a structure having an opening therein under said conductive layer and filling said opening with said conductive material to form said vertical component.]
 - filling said contact with a conducting material.